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RELIABILITY REPORT
FOR

DS21348, Rev C1

Dallas Semiconductor

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Conclusion:

The following qualification successfully meets the quality and reliability standards required of all Dallas Semiconductor products and processes:

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In addition, Dallas Semiconductor's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at http://www.maxim-ic.com/TechSupport /dsreliability.html.

Device Description:

A description of this device can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l_datasheet3.cfm.

Reliability Derating:

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

AfT = exp((Ea/k)*(1/Tu - 1/Ts)) = tu/ts
AfT = Acceleration factor due to Temperature
tu = Time at use temperature (e.g. 55°C)
ts = Time at stress temperature (e.g. 125°C)
k = Boltzmann's Constant (8.617 x 10-5 eV/°K)
Tu = Temperature at Use (°K)
Ts = Temperature at Stress (°K)
Ea = Activation Energy (e.g. 0.7 ev)

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

AfV = exp(B*(Vs - Vu))
AfV = Acceleration factor due to Voltage
Vs = Stress Voltage (e.g. 7.0 volts)
Vu = Maximum Operating Voltage (e.g. 5.5 volts)
B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

Fr = X/(ts * AfV * AfT * N * 2)
X = Chi-Sq statistical upper limit
N = Life test sample size

Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

MTTF = 1/Fr

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

FAILURE RATE: MTTF (YRS): 41831 FITS: 2.7

The parameters used to calculate this failure rate are as follows:

Cf: 60% Ea: 0.7 B: 0 Tu: 25 °C Vu: 5.5 Volts

The reliability data follows. A the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available.

Device Information:

Process:	D6H-2P2M,HPVt,TCZ ALOCOS:GOI
Passivation:	Laser/TEOS Ox - Pass/Nit - Gen.LaserPrb
Die Size:	205 x 209
Number of Transistors:	0
Interconnect:	Aluminum / 1% Silicon / 0.5% Copper
Gate Oxide Thickness:	150 Å

ELECTRICAL CHARACTERIZATION

DESCRIPTION	DATE CODE	CONDITION	READPOINT	QUANTITY	FAILS
ESD SENSITIVITY	0227	EOS/ESD S5.1 HBM 500 VOLTS	1 PUL'S	3	0
ESD SENSITIVITY	0227	EOS/ESD S5.1 HBM 1000 VOLTS	1 PUL'S	3	0
ESD SENSITIVITY	0227	EOS/ESD S5.1 HBM 2000 VOLTS	1 PUL'S	3	0
ESD SENSITIVITY	0227	EOS/ESD S5.1 HBM 4000 VOLTS	1 PUL'S	3	0
ESD SENSITIVITY	0227	EOS/ESD S5.1 HBM 8000 VOLTS	1 PUL'S	3	3
LATCH-UP	0227	JESD78, I-TEST 125C		3	0
LATCH-UP	0227	JESD78, Vsupply TEST 125C		3	0
			Total:		**3**

OPERATING LIFE

DESCRIPTION	DATE CODE	CONDITION	READPOINT	QUANTITY	FAILS
HIGH VOLTAGE LIFE	0227	125C, 6.0 VOLTS	1000 HRS	77	0
HIGH VOLTAGE LIFE	0307	125C, 6.0 VOLTS	1000 HRS	77	0
HIGH VOLTAGE LIFE	0310	125C, 6.0 VOLTS	1000 HRS	80	0
HIGH TEMP OP LIFE	0311	125C, 3.5 VOLTS	1000 HRS	77	0
HIGH TEMP OP LIFE	0312	125C, 3.3 VOLTS	1000 HRS	45	0
			Total:		**0**

STORAGE LIFE

DESCRIPTION	DATE CODE	CONDITION	READPOINT	QUANTITY	FAILS

STORAGE LIFE	0305	125C	1000	HRS	45	0
STORAGE LIFE	0309	125C	1000	HRS	45	0
STORAGE LIFE	0309	125C	1000	HRS	45	0
STORAGE LIFE	0312	125C	1000	HRS	42	0
STORAGE LIFE	0312	125C	1000	HRS	41	0
STORAGE LIFE	0312	150C	1000	HRS	77	0
				Total:		**0**

TEMPERATURE CYCLE

DESCRIPTION	DATE CODE	CONDITION	READPOINT		QUANTITY	FAILS
TEMP CYCLE	0305	-55C TO 125C	1000	CYS	45	0
TEMP CYCLE	0309	-55C TO 125C	1000	CYS	45	0
TEMP CYCLE	0309	-55C TO 125C	1000	CYS	45	0
TEMP CYCLE	0310	-55C TO 125C	1000	CYS	80	0
TEMP CYCLE	0312	-55C TO 125C	1000	CYS	45	0
TEMP CYCLE	0312	-55C TO 125C	1000	CYS	45	0
TEMP CYCLE	0312	-55C TO 125C	1000	CYS	76	0
				Total:		**0**

UNBIASED MOISTURE RESISTANCE

DESCRIPTION	DATE CODE	CONDITION	READPOINT		QUANTITY	FAILS
MOISTURE SOAK	0305	85 C/85% R.H.	1000	HRS	45	0
MOISTURE SOAK	0309	85 C/85% R.H.	1000	HRS	45	0
MOISTURE SOAK	0309	85 C/85% R.H.	1000	HRS	45	0
MOISTURE SOAK	0312	85 C/85% R.H.	1000	HRS	45	0
MOISTURE SOAK	0312	85 C/85% R.H.	1000	HRS	45	0
HAST	0312	130C, 85% R.H.	96	HRS	45	0
				Total:		**0**

FAILURE RATE: **MTTF (YRS): 41831** **FITS: 2.7**